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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Scott G. Meikle et al.

Title: METHOD OF DEPOSITING TUNGSTEN NITRIDE USING A SOURCE GAS COMPRISING SILICON

Docket No.: 303.444US5

Serial No.: 10/004,714

Filed: December 5, 2001

Due Date: October 18, 2002

Examiner: Ginette Peralta

Group Art Unit: 2814

Commissioner for Patents
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ An Amendment and Response (8 Pages).
- ☒ Clean Version of Pending Claims (6 pgs.).

Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on this 18th day of October, 2002.

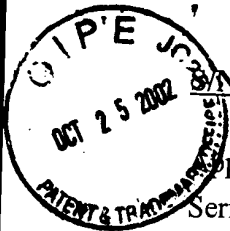
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8/N 10/004,714

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AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

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Applicant has reviewed the Office Action mailed on July 18, 2002. Please amend the above-identified patent application as follows.

IN THE CLAIMS

Please amend previously pending claims 41 - 42, 46, 49 - 50, 52, 55 - 56, 58, 61 - 64, 66 and 69 - 72 by substituting the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The specific amendments to individual claims are detailed in the following marked up set of claims.

41. (Amended) A capacitor, comprising:
a first electrode;
a second electrode; and
a dielectric disposed between the first and the second electrode,
wherein at least one of the first electrode and the second electrode includes [only] a tungsten nitride layer, and the tungsten nitride layer includes silicon.
42. (Amended) The capacitor of claim 41, wherein both the first electrode and the second electrode includes [only] a tungsten nitride layer, and the tungsten nitride layer includes silicon.
46. (Amended) A capacitor, comprising:
a first electrode;
a dielectric disposed on the first electrode; and